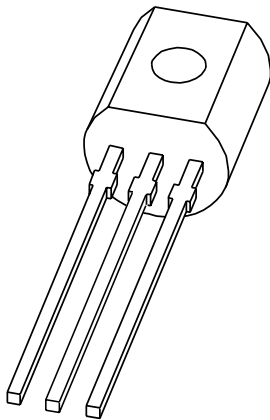


# DATA SHEET



## **BC237; BC237B** NPN general purpose transistors

Product specification  
Supersedes data of 1997 Mar 06  
File under Discrete Semiconductors, SC04

1997 Sep 04

# NPN general purpose transistors

# BC237; BC237B

### FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 45 V).

### APPLICATIONS

- General purpose switching and amplification.

### DESCRIPTION

NPN transistor in a TO-92; SOT54 plastic package.  
 PNP complements: BC307; BC307B.

### PINNING

PIN	DESCRIPTION
1	emitter
2	base
3	collector

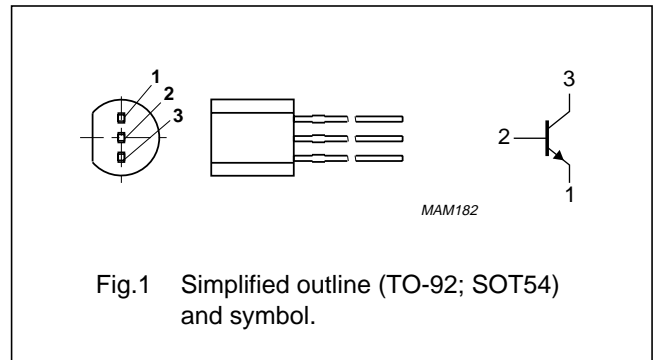


Fig.1 Simplified outline (TO-92; SOT54) and symbol.

### QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CBO}$	collector-base voltage	open emitter	–	50	V
$V_{CEO}$	collector-emitter voltage	open base	–	45	V
$I_{CM}$	peak collector current		–	200	mA
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ }^\circ\text{C}$	–	500	mW
$h_{FE}$	DC current gain	$I_C = 2\text{ mA}; V_{CE} = 5\text{ V}$			
	BC237		120	460	
	BC237B		200	460	
$f_T$	transition frequency	$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}; f = 100\text{ MHz}$	100	–	MHz

## NPN general purpose transistors

## BC237; BC237B

**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter	–	50	V
V <sub>CEO</sub>	collector-emitter voltage	open base	–	45	V
V <sub>EBO</sub>	emitter-base voltage	open collector	–	6	V
I <sub>C</sub>	collector current (DC)		–	100	mA
I <sub>CM</sub>	peak collector current		–	200	mA
I <sub>BM</sub>	peak base current		–	200	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	–	500	mW
T <sub>stg</sub>	storage temperature		–65	+150	°C
T <sub>j</sub>	junction temperature		–	150	°C
T <sub>amb</sub>	operating ambient temperature		–65	+150	°C

**Note**

1. Transistor mounted on an FR4 printed-circuit board.

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to ambient	note 1	250	K/W

**Note**

1. Transistor mounted on an FR4 printed-circuit board.

NPN general purpose transistors

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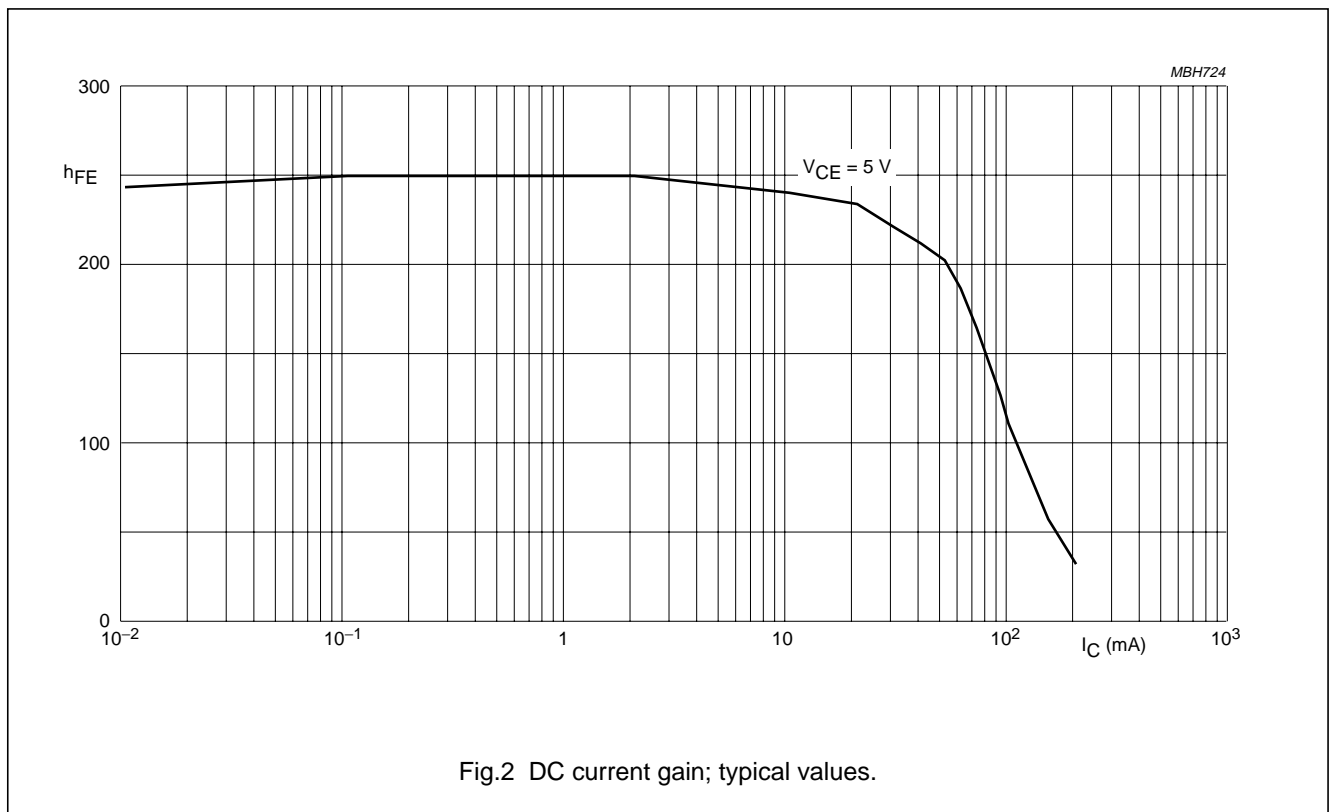
**CHARACTERISTICS**

T<sub>amb</sub> = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>CBO</sub>	collector cut-off current	I <sub>E</sub> = 0; V <sub>CB</sub> = 30 V	–	–	15	nA
		I <sub>E</sub> = 0; V <sub>CB</sub> = 30 V; T <sub>j</sub> = 150 °C	–	–	5	μA
I <sub>EBO</sub>	emitter cut-off current	I <sub>C</sub> = 0; V <sub>EB</sub> = 5 V	–	–	100	nA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> = 0.1 mA; V <sub>CE</sub> = 5 V; see Fig.2	–	250	–	
h <sub>FE</sub>	DC current gain BC237 BC237B	I <sub>C</sub> = 2 mA; V <sub>CE</sub> = 5 V; see Fig.2	120	–	460	
			200	–	460	
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = 100 mA; I <sub>B</sub> = 5 mA; note 1	–	–	600	mV
V <sub>BEsat</sub>	base-emitter saturation voltage	I <sub>C</sub> = 100 mA; I <sub>B</sub> = 5 mA	–	–	1200	mV
V <sub>BE</sub>	base-emitter voltage	I <sub>C</sub> = 2 mA; V <sub>CE</sub> = 5 V	580	–	700	mV
C <sub>c</sub>	collector capacitance	I <sub>E</sub> = i <sub>e</sub> = 0; V <sub>CB</sub> = 10 V; f = 1 MHz	–	11	–	pF
C <sub>e</sub>	emitter capacitance	I <sub>C</sub> = i <sub>c</sub> = 0; V <sub>EB</sub> = 0.5 V; f = 1 MHz	–	1.5	–	pF
f <sub>T</sub>	transition frequency	I <sub>C</sub> = 10 mA; V <sub>CE</sub> = 5 V; f = 100 MHz	100	–	–	MHz
F	noise figure	I <sub>C</sub> = 200 μA; V <sub>CE</sub> = 5 V; R <sub>S</sub> = 2 kΩ; f = 1 kHz; B = 200 Hz	–	–	10	dB

**Note**

1. Pulse test: t<sub>p</sub> ≤ 300 μs; δ ≤ 0.02.



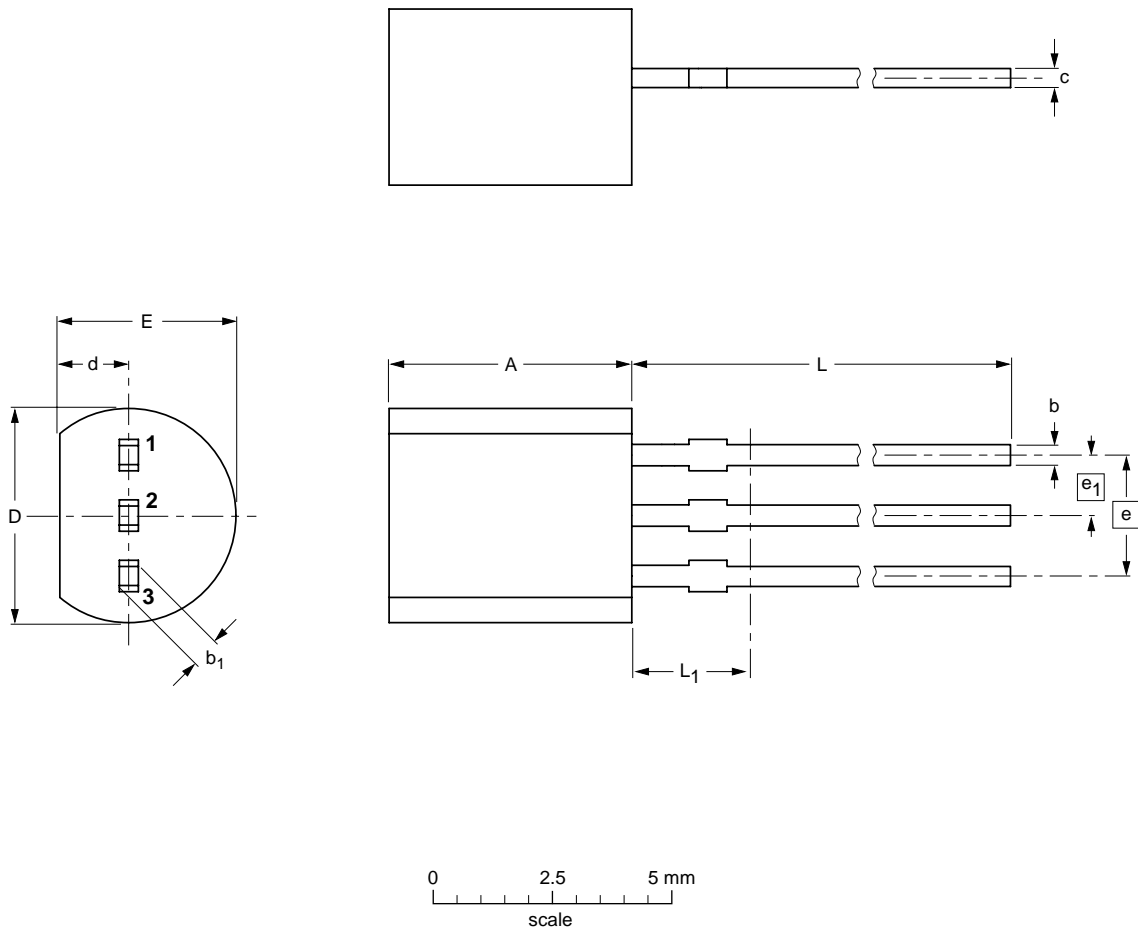
NPN general purpose transistors

BC237; BC237B

PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



DIMENSIONS (mm are the original dimensions)

UNIT	A	b	b <sub>1</sub>	c	D	d	E	e	e <sub>1</sub>	L	L <sub>1</sub> <sup>(1)</sup>
mm	5.2 5.0	0.48 0.40	0.66 0.56	0.45 0.40	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ		
SOT54		TO-92	SC-43		97-02-28

## NPN general purpose transistors

BC237; BC237B

**DEFINITIONS**

<b>Data Sheet Status</b>	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
<b>Limiting values</b>	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
<b>Application information</b>	
Where application information is given, it is advisory and does not form part of the specification.	

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NPN general purpose transistors

BC237; BC237B

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